



SSC8L32GN6

N-Channel Enhancement Mode MOSFET

➤ Features

VDS	VGS	RDSON Typ.	ID
30V	±20V	2.7mR@10V	95A
		3.7mR@4V5	

➤ Description

This device uses advanced trench technology to provide excellent RDSON and low gate charge. This device is suitable for use as a load switch or in PWM applications.

➤ Applications

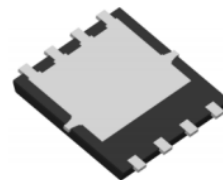
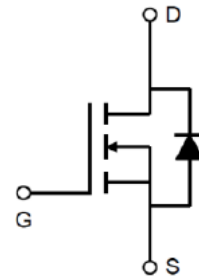
- Load Switch
- Portable Devices
- DCDC conversion

➤ Ordering Information

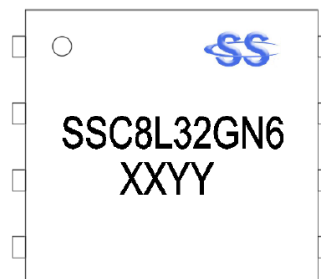
Device	Package	Shipping
SSC8L32GN6	PDFN5x6	5000/Reel

➤ Pin configuration

Top view



Bottom View



(XX: year/YY: week)

Marking



➤ **Absolute Maximum Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	30	V
V_{GSS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current ^a	95	A
I_{DM}	Pulsed Drain Current ^b	140	A
P_D	Power Dissipation ^c	70	W
P_{DSM}	Power Dissipation ^a	5.25	W
T_J	Operation junction temperature	-55 to 150	$^{\circ}\text{C}$
T_{STG}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a		39	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance		6.5	

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper,in a still air environment with $T_A=25^{\circ}\text{C}$.The value in any given application depends on the user is specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

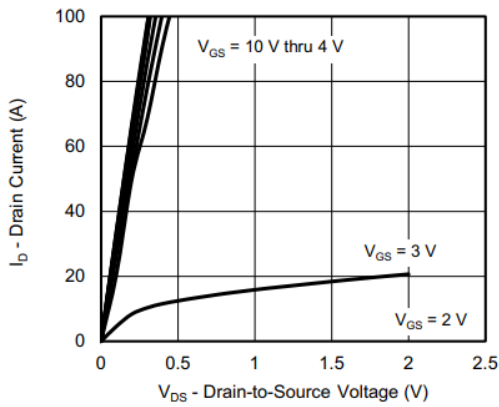


➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

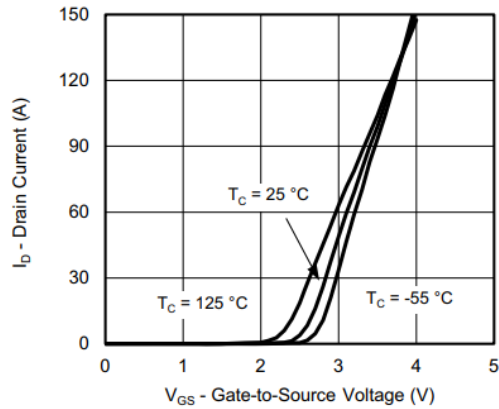
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250uA	30			V
VGS (th)	Gate Threshold Voltage	VDS=VGS, ID=250uA	1	1.5	2.2	V
RDS(on)	Drain-Source On- Resistance	VGS=10V, ID=20A		2.7	3	mR
		VGS=4.5V, ID=10A		3.7	4.5	
IDSS	Zero Gate Voltage Drain Current	VDS=30V, VGS=0V			1	uA
IGSS	Gate-Source leak current	VGS=±20V, VDS=0V			±100	nA
VSD	Forward Voltage	VGS=0V, IS=1A			1.3	V
Ciss	Input Capacitance	VDS=20V, VGS=0V, f=1MHZ		2550		pF
Coss	Output Capacitance			550		
Crss	Reverse Transfer Capacitance			110		
Qg	Total Gate Charge	VDS=15V , ID=20A , VGS=4.5V		29.5		nC
Qgs	Gate to source charge			6		
Qgd	Gate to drain charge			5.5		
TD(ON)	Turn-on delay time	VGEN=10V, VDS=15V, RL=15R,		10		ns
TD(OFF)	Turn-off delay time	RG=3R, ID=1A		25		



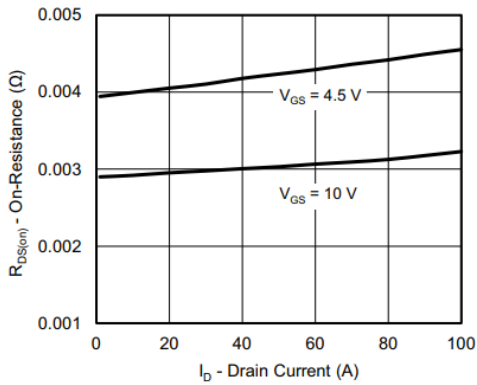
➤ **Typical Characteristics** ($T_A=25^\circ\text{C}$ unless otherwise noted)



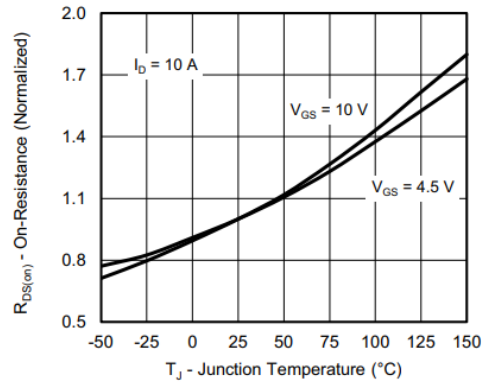
Output Characteristics



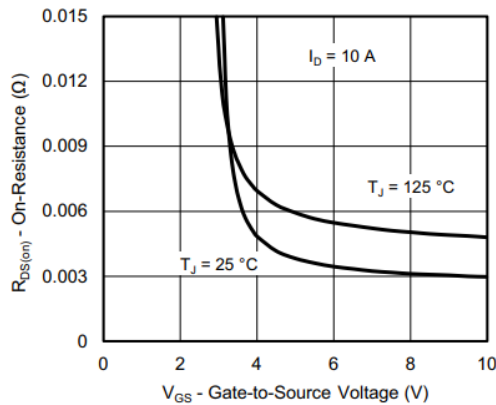
Transfer Characteristics



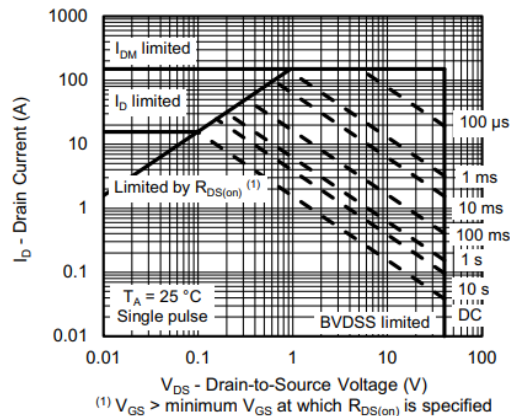
On-Resistance vs. Drain Current and Gate Voltage



On-Resistance vs. Junction Temperature



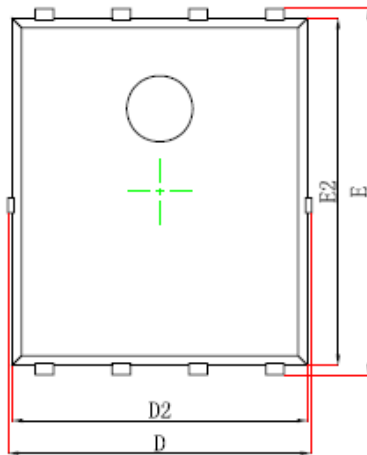
On-Resistance vs. Gate-to-Source Voltage



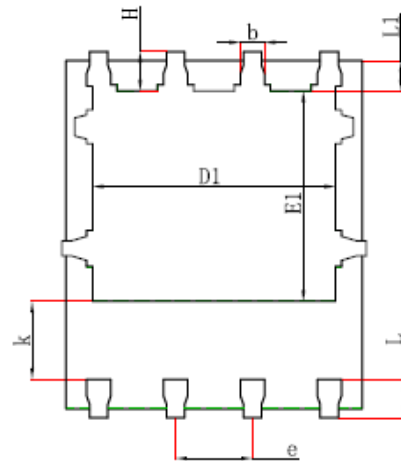
Safe Operating Area, Junction-to-Ambient



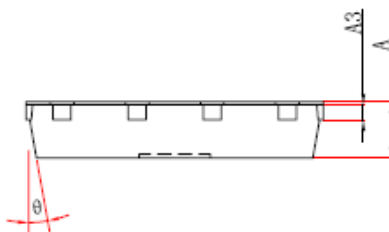
➤ Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Package : DNF5X6-8L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF		0.010REF	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°



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